

## ActiveQR™ Quasi-Resonant PWM Controller

### FEATURES

- Quasi-Resonant Operation
- Adjustable up to 150kHz Switching Frequency
- Accurate OCP/OLP Protection
- Integrated Patented Frequency Foldback Technique
- Integrated Patented Line and Primary Inductance Compensation
- Built-in Soft-Start Circuit
- Line Under-Voltage, Thermal, Output Over-voltage, Output Short Protections
- Current Sense Resistor Short Protection
- Transformer Winding Short Protection
- 100mW Standby Power
- Complies with Global Energy Efficiency and CEC Average Efficiency Standards
- Tiny SOT23-6 Packages

### APPLICATIONS

- AC/DC Adaptors/Chargers for Cell Phones, Cordless Phone, PDAs, E-books
- Adaptors for Portable Media Player, DSCs, Set-top boxes, DVD players, records
- Linear Adapter Replacements

### GENERAL DESCRIPTION

The ACT510 is a high performance peak current mode PWM controller. ACT510 applies *ActiveQR™* and frequency foldback technique to reduce EMI and improve efficiency. ACT510's maximum switching frequency is set at 150kHz. Very low standby power, good dynamic response and accurate voltage regulation is achieved with an opto-coupler and the secondary side control circuit.

The idle mode operation enables low standby power of 100mW with small output voltage ripple. By applying frequency foldback and *ActiveQR™* technology, ACT510 increases the average system efficiency compared to conventional solutions and

exceeds the latest ES2.0 efficiency standard with good margin.

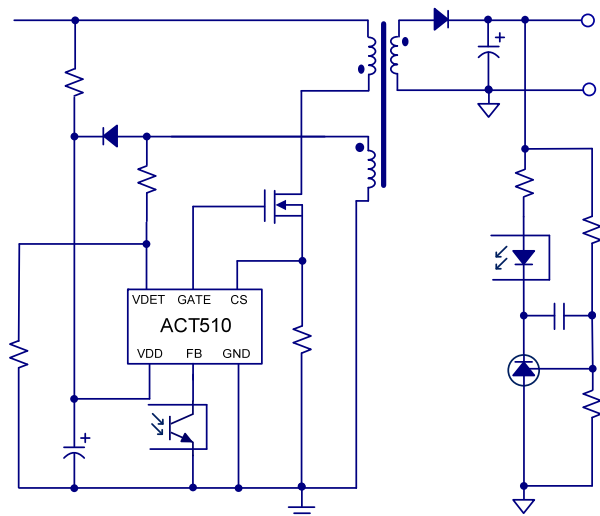
ACT510 integrates comprehensive protection. In case of over temperature, over voltage, winding short, current sense resistor short, open loop and overload conditions, it would enter into auto restart mode including Cycle-by-Cycle current limiting.

ACT510 is to achieve no overshoot and very short rise time even with a big capacitive load (4000 $\mu$ F) with the built-in fast and soft start process.

The Quasi-Resonant (QR) operation mode can improve efficiency, reduce EMI and further reduce the components in input filter.

ACT510 is ideal for applications up to 60 Watts.

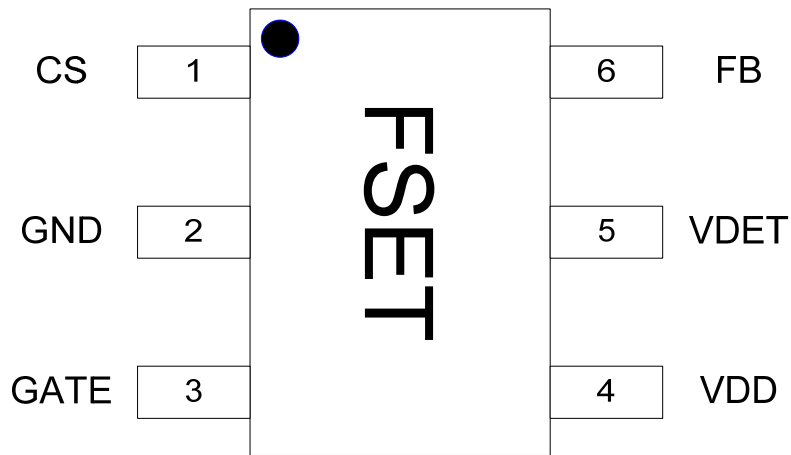
**Figure 1:**  
Simplified Application Circuit



## ORDERING INFORMATION

PART NUMBER	TEMPERATURE RANGE	PACKAGE	PINS	PACKING METHOD	TOP MARK
ACT510US-T	-40°C to 85°C	SOT23-6	6	TUBE & REEL	FSET

## PIN CONFIGURATION



**SOT23-6  
ACT510US**

## PIN DESCRIPTIONS

PIN	NAME	DESCRIPTION
1	CS	Current Sense Pin. Connect an external resistor ( $R_{CS}$ ) between this pin and ground to set peak current limit for the primary switch.
2	GND	Ground.
3	GATE	Gate Drive. Gate driver for the external MOSFET transistor.
4	VDD	Power Supply. This pin provides bias power for the IC during startup and steady state operation.
5	VDET	Valley Detector Pin. Connect this pin to a resistor divider network from the auxiliary winding to detect zero-crossing points for valley turn on operation.
6	FB	Feedback Pin. Connect this pin to optocouplers's collector for output regulation.

## ABSOLUTE MAXIMUM RATINGS<sup>①</sup>

PARAMETER	VALUE	UNIT
FB, CS, VDET to GND	-0.3 to + 6	V
VDD, GATE to GND	-0.3 to + 28	V
Maximum Power Dissipation (SOT23-6)	0.45	W
Operating Junction Temperature	-40 to 150	°C
Junction to Ambient Thermal Resistance ( $\theta_{JA}$ )	220	°C/W
Storage Temperature	-55 to 150	°C
Lead Temperature (Soldering, 10 sec)	300	°C

①: Do not exceed these limits to prevent damage to the device. Exposure to absolute maximum rating conditions for long periods.

## ELECTRICAL CHARACTERISTICS

( $V_{DD} = 13V$ ,  $L_M = 0.54mH$ ,  $R_{CS} = 1.37\Omega$ ,  $V_{OUT} = 5V$ ,  $N_P = 81$ ,  $N_S = 5$ ,  $N_A = 12$ ,  $T_A = 25^\circ C$ , unless otherwise specified.)

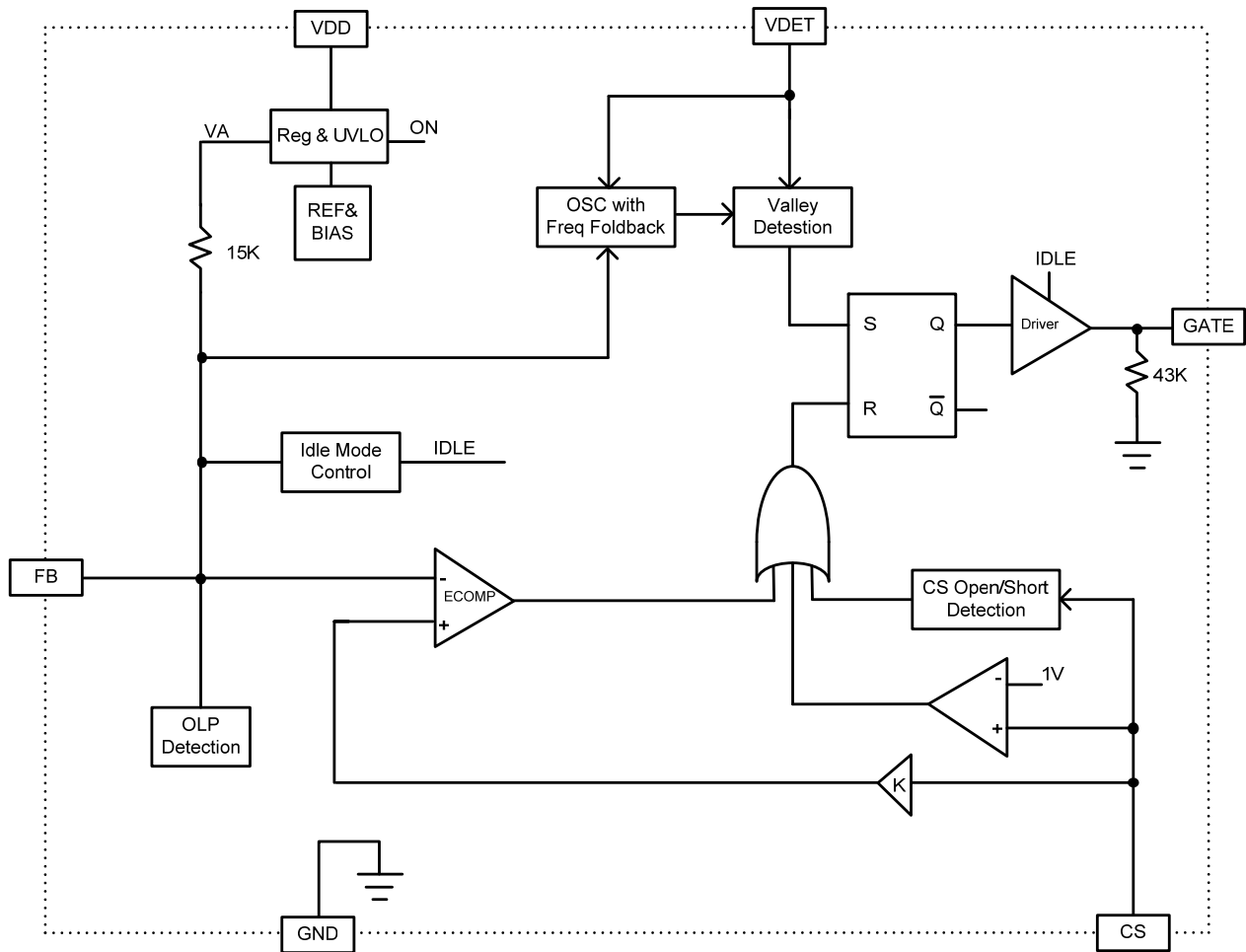
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Supply</b>						
VDD Turn-On Voltage	$V_{DDON}$	$V_{DD}$ Rising from 0V	11.16	12	12.84	V
VDD Turn-Off Voltage	$V_{DDOFF}$	$V_{DD}$ Falling after Turn-on	6.6	7.4	8.2	V
VDD Over Voltage Protection	$V_{DDOVP}$	$V_{DD}$ Rising from 0V		25		V
Start Up Supply Current	$I_{DDST}$	$V_{DD} = 10V$ , before VDD Turn-on		8	15	$\mu A$
IDD Supply Current	$I_{DD}$	$V_{DD} = 15V$ , after VDD Turn-on ,FB floating		0.6		mA
IDD Supply Current at Standby	$I_{DDSTBY}$	FB = 1.3V		0.4		mA
IDD Supply Current at Fault	$I_{DDFAULT}$	Fault mode, FB Floating		280		$\mu A$
<b>Feedback</b>						
FB Pull up Resistor	$R_{FB}$			15		k $\Omega$
CS to FB Gain	$A_{CS}$			3		V/V
VFB at Max Peak Current				$3 + V_{BE}$		V
FB Threshold to Stop Switching	$V_{FBBM1}$			$0.7 + V_{BE}$		V
FB Threshold to Start Switching	$V_{FBBM2}$			$0.75 + V_{BE}$		V
Output Overload Threshold				$3.5 + V_{BE}$		V
OverLoad/Over Voltage Blanking Time	$T_{OVBLANK}$			320		ms

## ELECTRICAL CHARACTERISTICS CONT'D

(V<sub>DD</sub> = 13V, L<sub>M</sub> = 0.54mH, R<sub>CS</sub> = 1.37Ω, V<sub>OUT</sub> = 5V, N<sub>P</sub> = 81, N<sub>S</sub> = 5, N<sub>A</sub> = 12, T<sub>A</sub> = 25°C, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Current Limit</b>						
CS Current Limit Threshold	V <sub>CSLIM</sub>		0.91	0.96	1.01	V
OLP Limit			95	100	105	%
Leading Edge Blanking Time	T <sub>CSBLANK</sub>		160	200	240	ns
<b>GATE DRIVE</b>						
Gate Rise Time	T <sub>RISE</sub>	V <sub>DD</sub> = 10V, CL = 1nF		200	250	ns
Gate Falling Time	T <sub>FALL</sub>	V <sub>DD</sub> = 10V, CL = 1nF		115	200	ns
Gate Low Level ON-Resistance	R <sub>ONLO</sub>	I <sub>SINK</sub> = 30mA		7		Ω
Gate High Level ON-Resistance	R <sub>ONHI</sub>	I <sub>SOURCE</sub> = 30mA		40		Ω
Gate Leakage Current		GATE = 25V, before V <sub>DD</sub> turn-on			1	μA
<b>Oscillator</b>						
Maximum Switching Frequency	f <sub>MAX</sub>		132	147	161	kHz
Switching Frequency Foldback	f <sub>MIN</sub>	FB = 2.3V + V <sub>BE</sub>		f <sub>MAX</sub> /3		kHz
Maximum Duty Cycle	D <sub>MAX</sub>		65	75		%
<b>Valley Detection</b>						
ZCD Threshold Voltage	V <sub>DETH</sub>			100		mV
Valley Detection Time Window		After valley detection time window, if no valley detected, forcedly turn-on main switch		5		μs
VDET Leakage Current					1	μA
<b>Protection</b>						
CS Short Waiting Time				1		μs
CS Short Detection Threshold				0.115		V
CS Open Threshold Voltage				1.73		V
Abnormal OCP Blanking Time				150		ns
Thermal Shutdown Temperature				135		°C
Line UVLO	I <sub>VDETVULO</sub>			0.2		mA
Line OVP	I <sub>VDETOVP</sub>			2		mA
VDET Over Voltage Protection	V <sub>DETVOVP</sub>			2.72		V
VDET Vo Short Threshold	V <sub>DETVOshort</sub>			0.58		V

## FUNCTIONAL BLOCK DIAGRAM



## FUNCTIONAL DESCRIPTION

ACT510 is a high performance peak current mode low-voltage PWM controller IC. The controller includes the most advance features that are required in the adaptor applications up to 60 Watt. Unique fast startup, frequency foldback, QR switching technique, accurate OLP, idle mode, external compensation adjustment, short winding protection, OCP, OTP, OVP and UVLO are included in the controller.

### Startup

Startup current of ACT510 is designed to be very low so that VDD could be charged to VDDON threshold level and device starts up quickly. A large value startup resistor can therefore be used to minimize the power loss yet reliable startup in application. For a typical AC/DC adaptor with universal input range design, two 1MΩ, 1/8 W startup resistors could be used together with a VDD capacitor(4.7uF) to provide a fast startup and yet low power dissipation design solution.

During startup period, the IC begins to operate with minimum Ippk to minimize the switching stresses for the main switch, output diode and transformers. And then, the IC operates at maximum power output to achieve fast rise time. After this, V<sub>OUT</sub> reaches about 90% V<sub>OUT</sub>, the IC operates with a 'soft-landing' mode(decrease Ippk) to avoid output overshoot.

### Constant Voltage (CV) Mode Operation

In constant voltage operation, the ACT510 regulates its output voltage through secondary side control circuit. The output voltage information is sensed at FB pin through OPTO coupling. The error signal at FB pin is amplified through TL431 and OPTO circuit. When the secondary output voltage is above regulation, the error amplifier output voltage decreases to reduce the switch current. When the secondary output voltage is below regulation, the error amplifier output voltage increases to ramp up the switch current to bring the secondary output back to regulation. The output regulation voltage is determined by the following relationship:

$$V_{OUTCV} = V_{REF\_TL431} \times \left(1 + \frac{R_{F1}}{R_{F2}}\right) \quad (1)$$

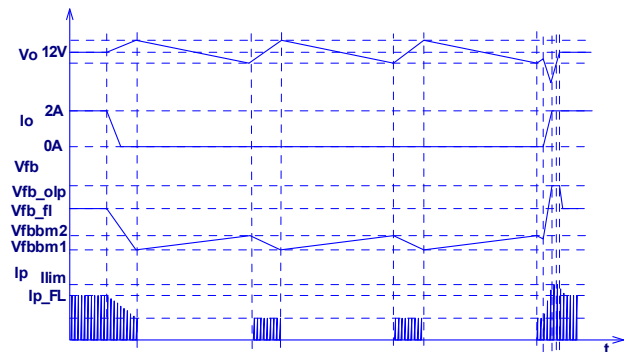
where R<sub>F1</sub> (R13) and R<sub>F2</sub> (R14) are top and bottom feedback resistor of the TL431.

### No Load Idle Mode

In no load standby mode, the feedback voltage falls below V<sub>FBBM2</sub> and reaches V<sub>FBBM1</sub>, ACT510 stop

switching. After it stops, as a result of a feedback reaction, the feedback voltage increases. When the feedback voltage reaches V<sub>FBBM2</sub>, ACT510 start switching again. Feedback voltage drops again and output voltage starts to bounds back and forward with very small output ripple. ACT510 leaves idle mode when load is added strong enough to pull feedback voltage exceed V<sub>FBBM2</sub>.

**Figure 2:**  
**Idle Mode**



### Primary Inductance Compensation

The ACT510 integrates a built-in primary inductance compensation circuit to maintain constant OLP despite variations in transformer manufacturing. The compensated ranges is +/-7%.

### Primary Inductor Current Limit Compensation

The ACT510 integrates a primary inductor peak current limit compensation circuit to achieve constant OLP over wide line and wide inductance.

### Frequency Foldback

When the load drops to 75% of full load level, ACT510 starts to reduce the switching frequency, which is proportional to the load current to improve the efficiency of the converter.

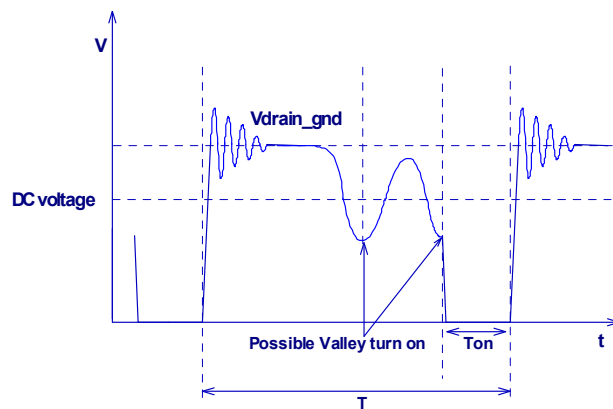
ACT510's load adaptive switching frequency enables applications to meet all latest green energy standards. The actual minimum average switching frequency is programmable with output capacitance, feedback circuit and dummy load (while still meeting standby power).

## FUNCTIONAL DESCRIPTION CONT'D

### Valley Switching

ACT510 employed valley switching from medium load to heavy load to reduce switching loss and EMI. In discontinuous mode operation, the resonant voltage between inductance and parasitic capacitance on MOSFET source pin is coupled by auxiliary winding and reflected on VDET pin through feedback network R6, R7. Internally, the VDET pin is connected to a zero-crossing detector to generate the switch turn on signal when the conditions are met.

**Figure 3:**  
**Valley Switching**



PROTECTION FUNCTIONS	FAILURE CONDITION	PROTECTION MODE
V <sub>DD</sub> Over Voltage	V <sub>DD</sub> > 25V (4 duty cycle)	Auto Restart
V <sub>VDET</sub> Over Voltage/No Voltage	V <sub>VD</sub> > 2.75V or No switching for 4 cycles	Auto Restart
Over Temperature	T > 135°C	Auto Restart
Short Winding/ Short Diode	V <sub>CS</sub> > 1.7V	Auto Restart
Over Load/Open Loop	I <sub>PK</sub> = I <sub>LIMIT</sub> or V <sub>FB</sub> = 3.5V + V <sub>BE</sub> for 320ms	Auto Restart
Output Short Circuit	V <sub>DET</sub> < 0.56V	Auto Restart
V <sub>DD</sub> Under Volt- age	V <sub>DD</sub> < 7.4V	Auto Restart

### Protection Features

The ACT510 provides full protection functions. The following table summarizes all protection functions.

#### **Auto-Restart Operation**

ACT510 will enter into auto-restart mode when a fault is identified. There is a startup phase in the auto-restart mode. After this startup phase the conditions are checked whether the failure is still present. Normal operation proceeds once the failure mode is removed. Otherwise, new startup phase will be initiated again.

To reduce the power loss during fault mode, the startup delay control is implemented. The startup delay time increases over lines.

## TYPICAL APPLICATION

### Design Example

The design example below gives the procedure for a DCM flyback converter using ACT510. Refer to application circuit Figure 5, the design for an adapter application starts with the following specification:

Input Voltage Range	90VAC - 265VAC, 50/60Hz
Output Power, P <sub>O</sub>	10W
Output Voltage, V <sub>OUTCV</sub>	5V
Full Load Current, I <sub>OUTFL</sub>	2A
OCP Current, I <sub>OUTMAX</sub>	2.3-2.6A
System Efficiency CV, η	0.78

The operation for the circuit shown in Figure 5 is as follows: the rectifier bridge BD1 and the capacitor C1/C2 convert the AC line voltage to DC bus voltage. This voltage supplies the primary winding of the transformer T1 and the startup circuit of R1/R2 and C4 to VDD pin of ACT510. The primary power current path is formed by the transformer's primary winding, Q1, and the current sense resistor R8. The resistors R3, R4, diode D4 and capacitor C3 create a snubber clamping network that protects Q1 from damage due to high voltage spike during Q1's turn off. The network consisting of capacitor C4, diode D2 and resistor R5 provides a VDD supply voltage for ACT510 from the auxiliary winding of the transformer. The resistor R5 is optional, which filters out spikes and noise to makes VDD more stable. C4 is the decoupling capacitor of the supply voltage and energy storage component for startup. During power startup, the current charges C4 through startup resistor R1/R2 from the rectified bus voltage. The diode D3 and the capacitor C6/L2/C7 rectify filter the output voltage. The resistor divider consists of R13 and R14 programs the output voltage. Since a bridge rectifier and bulk input capacitors are used, the resulting minimum and maximum DC input voltages can be calculated:

$$V_{INDC\_MIN} = \sqrt{2V_{INAC\_MIN}^2 - \frac{2P_{OUT} \left( \frac{1}{2f_L} - t_C \right)}{\eta \times C_{IN}}} \quad (2)$$

$$= \sqrt{2 \times 90^2 - \frac{2 \times 10 \times \left( \frac{1}{2 \times 47} - 3.5ms \right)}{0.78 \times 22 \mu F}} \approx 90V$$

$$V_{IN(MAX)DC} = \sqrt{2} \times V_{IN(MAX)AC} \quad (3)$$

$$= \sqrt{2} \times (265V_{AC}) = 375V$$

Where η is the estimated circuit efficiency, f<sub>L</sub> is the line frequency, t<sub>C</sub> is the estimated rectifier conduction time, C<sub>IN</sub> is empirically selected to be 22μF electrolytic capacitors.

The maximum duty cycle is set to be 45% at low line voltage 90VAC and the circuit efficiency is estimated to be 78%. Then the average input current is:

$$I_{IN\_MAX} = \frac{V_{OUT} \times I_{OUT\_FL}}{V_{INDC\_MIN} \times \eta} \quad (4)$$

$$= \frac{5 \times 2}{90 \times 0.78} = 142.5mA$$

The input primary peak current:

$$I_{ppk\_FL} = \frac{2 \times I_{IN}}{D_{MAX}} = \frac{2 \times 142.5mA}{0.45} = 633.3mA \quad (5)$$

The primary inductance of the transformer:

$$L_p = \frac{V_{IN} D_{MAX}}{I_{ppk\_FL} f_{sw}} = \frac{90 \times 0.45}{633.3mA \times 120kHz} = 0.54mH \quad (6)$$

The primary turn on time at full load:

$$T_{ON\_FL} = L_p \frac{I_{ppk\_FL}}{V_{INDC\_MIN}} \quad (7)$$

$$= \frac{0.54mH \times 633.3mA}{90} = 3.8\mu s$$

The ringing periods from primary inductance with mosfet drain-source capacitor:

$$T_{RINGING\_MAX} = 2\pi \sqrt{L_p C_{DS\_MAX}} \quad (8)$$

$$= 2 \times 3.14 \times \sqrt{0.54mH \times 100PF} = 1.46\mu s$$

To guarantee the valley turn on switching at full load, secondly reset time at full load can be calculated:

$$T_{RST} = T_{sw} - T_{ON\_FL} - 0.5T_{RINGING\_MAX} \quad (9)$$

$$= 1 / 120kHz - 3.8\mu s - 0.5 \times 1.46\mu s = 3.8\mu s$$

The minimum primary to secondary turn ratio N<sub>P</sub>/N<sub>S</sub>:

$$\frac{N_P}{N_S} = \frac{T_{ON\_FL}}{T_{RST}} \times \frac{V_{IN\_MIN}}{V_{OUT} + V_D} \quad (10)$$

$$= \frac{3.8}{3.8} \times \frac{90}{5 + 0.45} = 16.5$$



## TYPICAL APPLICATION CONT'D

The auxiliary to secondary turn ratio  $N_A/N_S$ :

$$\frac{N_A}{N_S} = \frac{V_{DD} + V_D'}{V_{OUT} + V_D} = \frac{13 + 0.45}{5 + 0.45} = 2.47 \quad (11)$$

EE16 core is selected for the transformer. The gapped core with an effective inductance  $A_{LE}$  of 82 nH/T<sup>2</sup> is selected. The turn of the primary winding is:

$$N_P = \sqrt{\frac{L_P}{A_{LE}}} = \sqrt{\frac{0.54 \text{ mH}}{82 \text{ nH} / T^2}} = 81 T \quad (12)$$

The turns of secondary and auxiliary winding can be derived accordingly:

$$N_S = \frac{N_s}{N_p} \times N_p = \frac{1}{16.5} \times 81 = 5T \quad (13)$$

$$N_A = \frac{N_A}{N_S} \times N_S = 2.47 \times 5 = 12T \quad (14)$$

Determining the value of the current sense resistor (R7) uses the maximum current in the design. So the input primary maximum current at maximum load:

$$I_{p\_OCP} = \sqrt{\frac{2 \times I_{OUT\_OCP} \times V_{OUT}}{L_p \times f_{sw} \times \eta}} = \sqrt{\frac{2 \times 2.6 \times 5}{0.54 \times 120 \times 0.78}} = 717 \text{ mA} \quad (15)$$

Since the ACT510 internal current limit is set to 0.96V, the design of the current sense resistor is given by:

$$R_{CS} = \frac{V_{CS}}{I_{p\_OCP}} = \frac{0.96}{0.717} = 1.37 \Omega \quad (16)$$

The voltage feedback resistors are selected according to the design. Because the line UVLO is 60VDC, the upper feedback resistor is given by:

$$\begin{aligned} R_{FB\_UP} &= V_{INDC\_UVLO} \times \frac{N_A}{N_p \times I_{FB\_UVLO}} \\ &= \frac{60 \times 12}{81 \times 0.2 \text{ mA}} = 46.4 \text{ k}\Omega \end{aligned} \quad (17)$$

The lower feedback resistor is selected as:

$$\begin{aligned} R_{FB\_LOW} &= \frac{V_{FB}}{(V_{OUT} + V_D) \frac{N_A}{N_S} - V_{FB}} R_{FB\_UP} \\ &= \frac{2.2}{(5 + 0.45) \times 1 - 2.2} \times 46.4 \text{ k}\Omega = 9.1 \text{ k}\Omega \end{aligned} \quad (18)$$

When selecting the output capacitor, a low ESR electrolytic capacitor is recommended to minimize ripple from the current ripple. The approximate

equation for the output capacitance value is given by:

$$C_{OUT} = \frac{I_{OUT}}{f_{sw} \times V_{RIPPLE}} = \frac{2}{120 \text{ k} \times 50 \text{ mV}} = 330 \mu\text{F} \quad (19)$$

Two 680μF electrolytic capacitors are used to further reduce the output ripple.

### PCB Layout Guideline

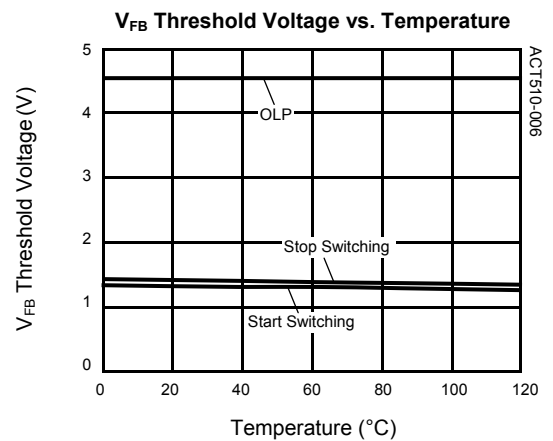
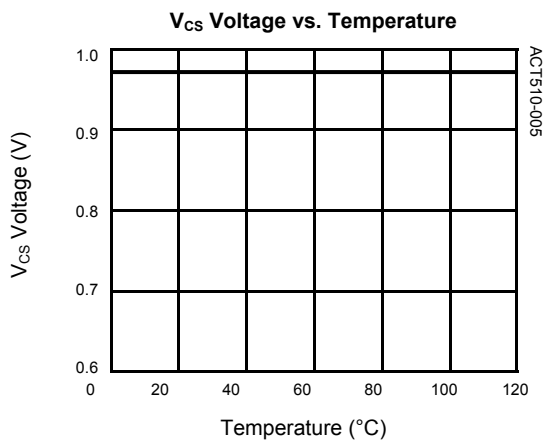
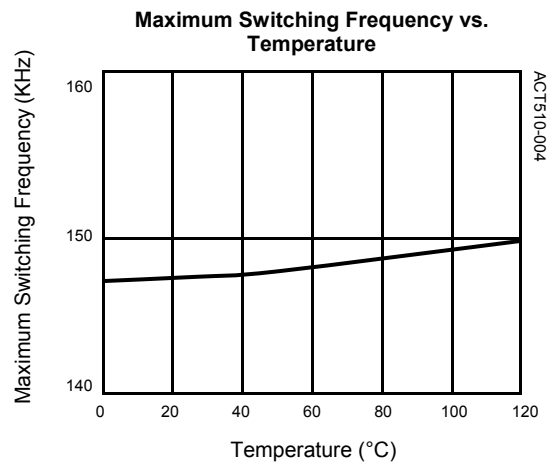
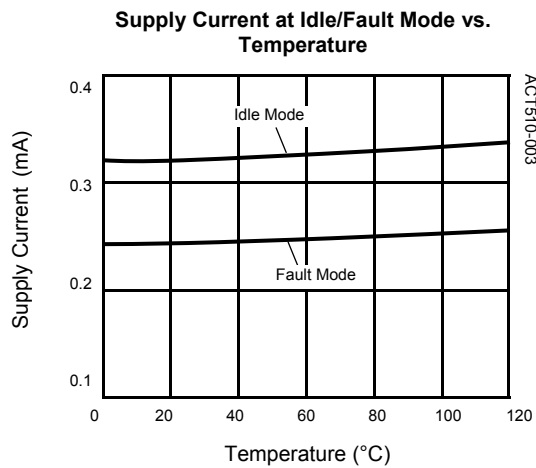
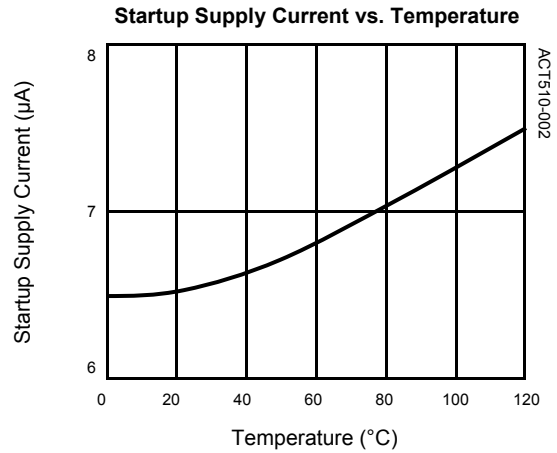
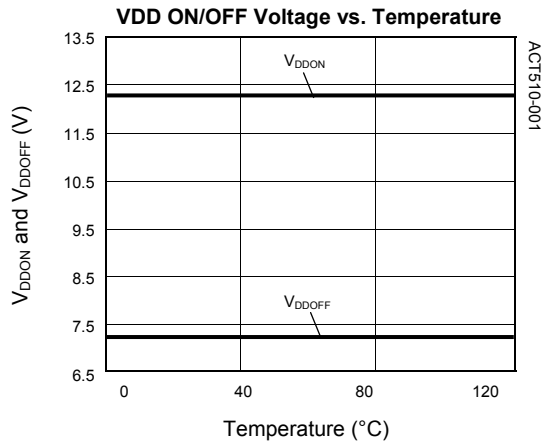
Good PCB layout is critical to have optimal performance. Decoupling capacitor (C4) and feedback resistor (R6/R7) should be placed close to VDD and FB pin respectively. There are two main power path loops. One is formed by C1/C2, primary winding, mosfet transistor and current sense resistor (R8). The other is secondary winding, rectifier D3 and output capacitors (C6/C7). Keep these loop areas as small as possible. Connecting high current ground returns, the input capacitor ground lead, and the ACT510 GND pin to a single point (star ground configuration).



**Table 1:**  
**ACT510 5V10W Bill of Materials**

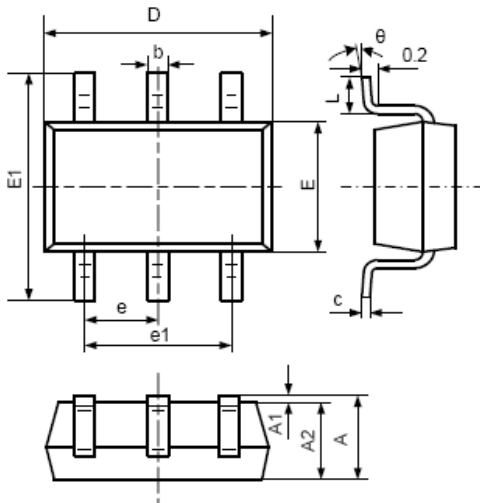
ITEM	REFERENCE	DESCRIPTION	QTY	MANUFACTURER
1	U1	IC, ACT510, SOT23-6	1	Active-Semi
2	C1	Capacitor, Electrolytic, 15µF/400V, 12x16mm	1	RUBYCON
3	C2	Capacitor, Electrolytic, 10µF/400V, 10x15mm	1	RUBYCON
4	C3	Capacitor, Ceramic, 1000pF/500V, 0805,SMD	1	POE
5	C4	Capacitor, Electrolytic, 6.8µF/35V, 5x11mm	1	POE
6	C5	Capacitor, Ceramic, 1000PF/100V, 0805,SMD	1	POE
7	C6	Capacitor, Electrolytic, 330µF/6.3V, 6.3x8mm	1	KSC
8	C7	Capacitor, Electrolytic, 820µF/6.3V, 6.5x15mm	1	KSC
9	C8	Capacitor, Ceramic, 0.1µF/25V, 0805, SMD	1	POE
10	C9	Capacitor, Ceramic, 1000pF/25V, 0805, SMD	1	POE
11	CY1	Safety Y1, Capacitor, 1000pF/400V, Dip	1	UXT
12	BD1	Bridge Rectifier, D1010S, 1000V/1.0A, SDIP	1	PANJIT
13	D2	Fast Recovery Rectifier, RS1G, 200V/1.0A, RMA	1	PANJIT
14	D3	Diode, Schottky, 45V/10A, S10U45S, SMD	1	Diodes
15	D4	Fast Recovery Rectifier, RS1M, 1000V/1.0A, RMA	1	PANJIT
16	D5	Diode,Ultra Fast, LL4148, SMD Open	1	Good-Ark
17	L1	Axial Inductor, 1.5mH, 5*7, Dip	1	SoKa
18	L2	Axial Inductor, 0.55*5T, 5*7, Dip	1	SoKa
19	LF2	CM Filter,R6K, 500µH, 0.55*2 6T	1	SoKa
20	Q1	Mosfet Transistor, 4N60, TO-262	1	Infineon
21	PCB1	PCB, L*W*T=53x29x1.6mm, Cem-1, Rev:A	1	Jintong
22	F1	Fuse, 1A/250V	1	TY-OHM
23	R1,R2	Chip Resistor, 1.0MΩ 1206, 5%	2	TY-OHM
24	R3	Carbon Resistor, 750KΩ, 0805, 5%	1	TY-OHM
25	R4	Chip Resistor, 100Ω, 0805, 5%	1	TY-OHM
26	R5, R9, R15	Chip Resistor, 22Ω, 0805, 5%	3	TY-OHM
27	R6	Chip Resistor, 46.4KΩ, 0805,1%	1	TY-OHM
28	R7	Chip Resistor, 9.1KΩ, 0805, 1%	1	TY-OHM
29	R8	Chip Resistor, 1.37Ω, 1206 , 5%	1	TY-OHM
30	R10, R11	Chip Resistor, 1KΩ, 0805, 5%	2	TY-OHM
31	R12	Chip Resistor, 3KΩ, 0805, 5%	1	TY-OHM
32	R13	Chip Resistor, 10.7KΩ, 0805, 1%	1	TY-OHM
33	R14	Chip Resistor, 10.5KΩ, 0805, 1%	1	TY-OHM
34	R16	Chip Resistor, 10Ω, 0805, 5%	1	TY-OHM
35	R17	Chip Resistor, 2.2KΩ, 0805, 5%	1	TY-OHM
36	T1	Transformer, Lp=0.54mH, EE16	1	
37	U2	OPOT PC817C	1	Sharp
38	IC3	TL431 TO-92	1	ST

## TYPICAL PERFORMANCE CHARACTERISTICS



## PACKAGE OUTLINE


### SOT23-6 PACKAGE OUTLINE AND DIMENSIONS



SYMBOL	DIMENSION IN MILLIMETERS		DIMENSION IN INCHES	
	MIN	MAX	MIN	MAX
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.700 REF		0.028 REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Active-Semi, Inc. reserves the right to modify the circuitry or specifications without notice. Users should evaluate each product to make sure that it is suitable for their applications. Active-Semi products are not intended or authorized for use as critical components in life-support devices or systems. Active-Semi, Inc. does not assume any liability arising out of the use of any product or circuit described in this datasheet, nor does it convey any patent license.

Active-Semi and its logo are trademarks of Active-Semi, Inc. For more information on this and other products, contact [sales@active-semi.com](mailto:sales@active-semi.com) or visit <http://www.active-semi.com>.

 is a registered trademark of Active-Semi.